

S/N 10/602,315

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.
Serial No.: 10/602,315
Filed: June 24, 2003
Name: LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS

Examiner: Asok K. Sarkar
Group Art Unit: 2891
Docket: 1303.107US1



COMMUNICATION CONCERNING RELATED APPLICATION(S)

Mail Stop RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date/Issue Date</u>	<u>Attorney Docket</u>	<u>Title</u>
11/036296	January 14, 2005	1303.030US2	LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO ₃ GATE DIELECTRICS
10/909959	August 2, 2004	1303.114US1	ATOMIC LAYER DEPOSITION OF ZIRCONIUM-DOPED TANTALUM OXIDE FILMS
10/931533	August 31, 2004	1303.119US1	ATOMIC LAYER DEPOSITED TITANIUM ALUMINUM OXIDE FILMS
10/926812	August 26, 2004	1303.121US1	RUTHENIUM GATE FOR A LANTHANIDE OXIDE DIELECTRIC LAYER
10/930167	August 31, 2004	1303.122US1	ATOMIC LAYER DEPOSITED LANTHANUM ALUMINUM OXIDE DIELECTRIC LAYER
11/010529	December 13, 2004	1303.126US1	ATOMIC LAYER DEPOSITED LANTHANUM HAFNIUM OXIDE DIELECTRICS
11/029757	January 5, 2005	1303.127US1	ATOMIC LAYER DEPOSITED HAFNIUM TANTALUM OXIDE DIELECTRICS
11/010766	December 13, 2004	1303.129US1	HYBRID ALD-CVD OF Pr _x YO _y /ZrO ₂ FILMS AS GATE DIELECTRICS
11/053577	February 8, 2005	1303.131US1	ATOMIC LAYER DEPOSITION OF DY-DOPED HfO ₂ FILMS AS GATE DIELECTRICS
11/058563	February 15, 2005	1303.133US1	ATOMIC LAYER DEPOSITION OF Zr ₃ N ₄ /ZrO ₂ FILMS AS GATE DIELECTRICS
11/063717	February 23, 2005	1303.134US1	ATOMIC LAYER DEPOSITION OF Hf ₃ N ₄ /HfO ₂ FILMS AS GATE

DIELECTRICS			
11/031289	January 7, 2005	1303.069US3	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS BY PLASMA OXIDATION
11/059594	February 16, 2005	1303.046US2	EVAPORATED LaAlO ₃ FILMS FOR GATE DIELECTRICS
11/092072	March 29, 2005	1303.135US1	ALD OF AMORPHOUS LANTHANIDE DOPED TIO _x FILMS
11/093104	March 29, 2005	1303.136US1	ATOMIC LAYER DEPOSITED TITANIUM SILICON OXIDE FILMS
11/117121	April 28, 2005	1303.138US1	ATOMIC LAYER DEPOSITED ZIRCONIUM SILICON OXIDE FILMS
11/117125	April 28, 2005	1303.139US1	ATOMIC LAYER DEPOSITION OF A RUTHENIUM LAYER TO A LANTHANIDE OXIDE DIELECTRIC LAYER
11/084968	March 21, 2005	1303.083US2	Zr-Sn-Ti-O FILMS
11/148505	June 9, 2005	1303.061US2	ATOMIC LAYER DEPOSITED NANOLAMINATES OF HfO ₂ /ZrO ₂ FILMS AS GATE DIELECTRICS

Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicants request that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.

Respectfully submitted,
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Date 6 July 2005 By David R. Cochran
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Mail Stop RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 6 day of July, 2005.

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